# PIP3224-DC Dual channel high-side TOPFET™ Rev. 01 — 20 February 2004

**Product data** 

## 1. Product profile

### 1.1 Description

Monolithic temperature and overload protected dual high-side power switch based on TOPFET<sup>™</sup> Trench technology in a 7-pin surface mount plastic package.

### **1.2 Features**

- Very low quiescent current
- Power TrenchMOS<sup>™</sup>
- Overtemperature protection
- Over and undervoltage protection
- Reverse battery protection
- Low charge pump noise
- Loss of ground protection
- Negative load clamping

### **1.3 Applications**

- 12 and 24 V grounded loads
- Inductive loads

- CMOS logic compatibility
- Current limitation
- Latched overload protection
- ESD protection for all pins
- Diagnostic status indication
- Off-state open load detection
- Load dump protection
- Internal ground resistor.
- High inrush current loads
- Replacement for relays and fuses.

#### 1.4 Quick reference data

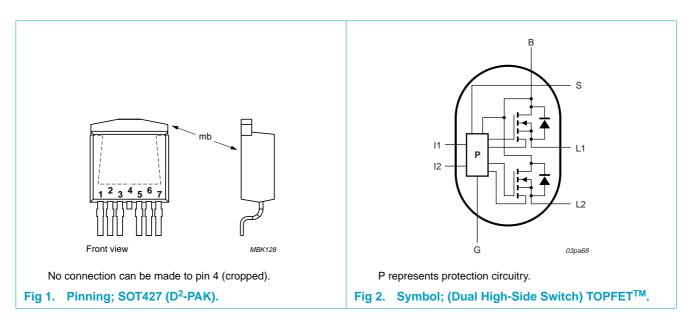
#### Table 1: Quick reference data

Symbol	Parameter	Min	Max	Units
R <sub>BLon</sub>	battery-load on-state resistance	-	90	mΩ
۱L	load current	-	4	А
I <sub>L(nom)</sub>	nominal load current (ISO)	3.6	-	А
I <sub>L(lim)</sub>	self-limiting load current	8	16	А
V <sub>BG(oper)</sub>	battery-ground operating voltage	5.5	35	V



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## 2. Pinning information



## 2.1 Pin description

Table 2:	Pin description			
Symbol	Pin	I/O		Description
L1	1	0		load 1
G	2	-		circuit common ground
11	3	I		input 1
В	4	-	[1] [2]	battery
S	5	0		status
12	6	I		input 2
L2	7	0		load 2
-	mb	-	[2]	mounting base

[1] Pin 4 is cropped and cannot be connected to the PCB by surface mounting.

[2] The battery is connected to the mounting base.

## 3. Ordering information

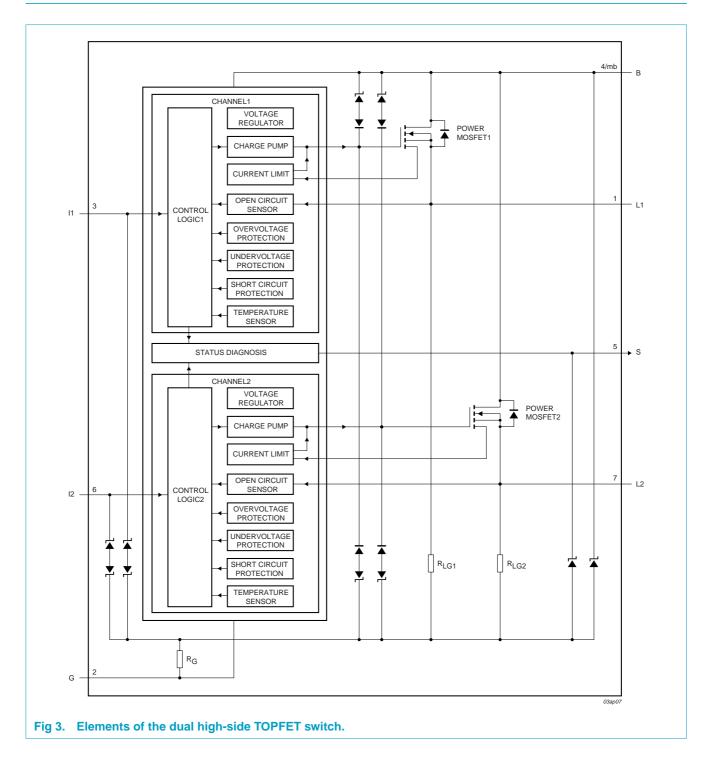
Table 3: Ordering infor	mation
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Type number	Package		
	Name	Description	Version
PIP3224-DC	D <sup>2</sup> -PAK	Plastic single-ended surface mounted package (Philips version of D <sup>2</sup> -PAK); 7 leads (one lead cropped)	SOT427

9397 750 12362 Product data

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## 4. Block diagram



## 5. Functional description

A diagnostic status ensures faster fault detection.

Active current limit is combined with latched short circuit protection in order to protect the device in the event of a short circuit.

Thermal shutdown for high temperature conditions has an automatic restart at a lower temperature so providing protection against excessive power dissipation.

Active clamping protects the device against low energy spikes.

Undervoltage lockout means the device shuts down for low battery voltages, thus avoiding faulty operation.

Overvoltage shutdown in the on-state protects a load such as a lamp filament from potentially destructive voltage spikes.

#### Table 4: Truth table

Abbreviations: L = logic LOW; H = logic HIGH; X = don't care; 0 = condition not present; 1 = condition present; UV = undervoltage; OV = overvoltage; OC = open circuit load; SC = short circuit; OT = overtemperature <sup>[1]</sup>.

Inp	out	Sup	ply		Load 1			Load 2	2	Load	output	Status	Operating mode
1	2	UV	ov	ОС	SC	ОТ	ос	SC	ОТ	1	2		
L	L	0	Х	0	Х	Х	0	Х	Х	OFF	OFF	Н	both off & normal
L	L	0	Х	1	Х	Х	Х	Х	Х	OFF	OFF	L	both off, one/both OC or shorted to V <sub>S</sub> or battery; Figure 10
L	Н	0	Х	1	Х	Х	0	0	0	OFF	ON	L	one off & OC, with other on & normal
Н	L	0	0	0	0	0	0	0	0	ON	OFF	Н	one on & normal, with other off & normal
Н	Н	0	0	0	0	0	0	0	0	ON	ON	Н	both on & normal
Н	Х	1	0	Х	Х	Х	0	Х	Х	OFF	OFF	Н	supply undervoltage lockout
Н	Х	0	1	Х	0	0	Х	0	0	OFF	OFF	Н	supply overvoltage shutdown
Н	Х	0	0	0	1	Х	Х	Х	Х	OFF	Х	L	one SC tripped
Н	L	0	0	0	1	Х	0	0	Х	OFF	OFF	L	one SC tripped, with other off & normal
Н	Н	0	0	0	1	Х	0	0	0	OFF	ON	L	one SC tripped, with other on & normal
Н	Х	0	0	0	0	1	Х	Х	Х	OFF	Х	L	one OT shutdown
Н	L	0	0	0	0	1	0	0	Х	OFF	OFF	L	one OT shutdown, with other off & normal
Н	Η	0	0	0	0	1	0	0	0	OFF	ON	L	one OT shutdown, with other on & normal

[1] The status will continue to indicate OT (even if the input goes LOW) until the device cools below the reset threshold temperature. See "Overtemperature protection" characteristics in Table 7 "Static characteristics".

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## 6. Limiting values

#### Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>BG</sub>	battery-ground supply voltage		[1]	-	45	V
۱ <sub>L</sub>	load current	$T_{mb} \le 130 \ ^{\circ}C$		-	4	А
P <sub>tot</sub>	total power dissipation	$T_{mb} \le 25 \ ^{\circ}C$		-	44.6	W
T <sub>stg</sub>	storage temperature			-55	+175	°C
Т <sub>ј</sub>	junction temperature			-40	+150	°C
T <sub>mb</sub>	mounting base temperature	during soldering ( $\leq$ 10 s)		-	260	°C
Reverse b	attery voltage					
V <sub>BGR</sub>	reverse battery-ground supply voltage	$R_l \geq 3.3 \; k\Omega; \; R_{SS} \geq 3.3 \; k\Omega; \; Figure \; 10$	[2]	-	16	V
V <sub>BGRR</sub>	repetitive reverse battery-ground supply voltage			-	32	V
Input curre	ent					
I	input current			-5	+5	mA
I <sub>IRM</sub>	repetitive peak input current	$\delta \leq 0.1;  t_p = 300 \; \mu s$		-50	+50	mA
Status cur	rent					
ls	status current			-5	+5	mA
I <sub>SRM</sub>	repetitive peak status current	$\delta \leq$ 0.1; $t_p$ = 300 $\mu s$		-50	+50	mA
Inductive	oad clamping					
E <sub>BL(CL)S</sub>	non-repetitive battery-load clamping energy	$T_j = 150 \text{ °C}$ prior to turn-off; $V_{BG} = 13 \text{ V}$ ; $I_L = 5 \text{ A}$ ; (one channel) Figure 13		-	60	mJ
Electrosta	tic discharge voltage					
V <sub>esd</sub>	electrostatic discharge voltage	Human Body Model 1; C = 100 pF; R = 1.5 k $\Omega$		-	2	kV

[1] The device will not be harmed by exposure to the maximum supply voltage, but normal operation is not possible because of overvoltage shutdown - see Table 7 "Static characteristics" for the operating range.

[2] Reverse battery voltage is only allowed with external resistors to limit the input and status currents to a safe value. The connected load must limit the reverse load current. The internal ground resistor limits the reverse battery ground current. See Figure 10 "Typical dynamic response circuit diagram including reverse supply protection and open load detection."

## 7. Thermal characteristics

#### **Thermal characteristics** Table 6: Conditions Symbol Parameter Min Тур Max Unit thermal resistance from junction to per channel 4 5.6 K/W R<sub>th(j-mb)</sub> mounting base K/W both channels 2 2.8 thermal resistance from junction to mounted on printed circuit board; 50 K/W R<sub>th(j-a)</sub> \_ ambient minimum footprint

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## 8. Static characteristics

#### Table 7: Static characteristics

Limits are valid for  $-40 \circ C \leq T_{mb} \leq +150 \circ C$  and typical values for  $T_{mb} = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Uni
Clamping	voltage						
V <sub>BG(CL)</sub>	battery-ground clamping voltage	I <sub>G</sub> = 1 mA		45	55	65	V
V <sub>BL(CL)</sub>	battery-load clamping voltage	$I_L = I_G = 1 \text{ mA}$		50	55	65	V
V <sub>LG(CL)</sub>	load-ground clamping voltage	I <sub>L</sub> = 10 mA; Figure 13	[1]	-18	-23	-28	V
		$I_L = 4 \text{ A}; t_p = 300 \ \mu \text{s}$		-20	-25	-30	V
Supply vo	Itage						
V <sub>BG(oper)</sub>	battery-ground operating voltage			5.5	-	35	V
Current <sup>[2]</sup>							
I <sub>B</sub>	battery quiescent current	$V_{LG} = V_{IG} = 0 V$ ; Figure 9	[3]				
		T <sub>mb</sub> = 150 °C		-	-	20	μΑ
		T <sub>mb</sub> = 25 °C		-	0.1	1	μΑ
I <sub>L(off)</sub>	off-state load current	$V_{BL} = V_{BG}$ ; per channel					
		T <sub>mb</sub> = 150 °C		-	-	10	μΑ
		T <sub>mb</sub> = 25 °C		-	0.1	1	μΑ
I <sub>G(on)</sub>	operating current	one channel on; Figure 5		-	2	3	mA
		both channels on		-	4	6	mA
I <sub>L(nom)</sub>	nominal load current (ISO)	$V_{BL}$ = 0.5 V; $T_{mb}$ = 85 °C	[4]	3.6	-	-	А
Resistanc	e						
R <sub>BLon</sub>	battery-load on-state resistance	$9 \le V_{BG} \le 35$ V; I <sub>L</sub> = 4 A; Figure 4	[5]				
		T <sub>mb</sub> = 25 °C		-	73	90	mΩ
		T <sub>mb</sub> = 150 °C		-	73 90 146 180	mΩ	
		$V_{BG} = 5.5 \text{ V}; \text{ I}_{L} = 4 \text{ A}$					
		T <sub>mb</sub> = 25 °C		-	76	120	mΩ
		T <sub>mb</sub> = 150 °C		-	150	10 1 3 6 - 90 180 120 240 100 160 8.5	mΩ
R <sub>G</sub>	ground resistor	$I_G = -200 \text{ mA}; t_p = 300 \ \mu s$	[6]	40	75	100	Ω
Input <sup>[7]</sup>							
I	input current	$V_{IG} = 5 V$		20	60	160	μΑ
V <sub>IG(CL)</sub>	input-ground clamping voltage	$I_I = 200 \ \mu A$		5.5	7	8.5	V
V <sub>IG(on)</sub>	input-ground turn-on voltage	Figure 8		-	2.1	3	V
V <sub>IG(off)</sub>	input-ground turn-off voltage			1.2	1.8	-	V
V <sub>IG(on)(hys)</sub>	input-ground turn-on hysteresis			0.15	0.3	0.5	V
I <sub>I(on)</sub>	input turn-on current	V <sub>IG</sub> = 3 V		-	-	100	μA
I <sub>I(off)</sub>	input turn-off current	V <sub>IG</sub> = 1.2 V		12	-	-	μΑ
Open curr	ent detection <sup>[8][9]</sup>						
V <sub>LG(oc)</sub>	load-ground open circuit voltage	$V_{BG} \ge 9 V$		1.5	2.5	3.5	V
I <sub>G(oc)</sub>	open-circuit operating current	$V_{BG} = V_{LG} = 16 V$		-	0.8	1.5	mA
		open load detected; other					

channel is off

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>L(oc)</sub>	load open circuit current	$V_{LG} = 3.5 V$ ; per channel		-	-22	-40	μΑ
		V <sub>LG</sub> = 16 V; per channel		-	-200	-300	μΑ
R <sub>L(oc)</sub>	open circuit load resistor	V <sub>S</sub> = 5 V; connected externally; per channel; Figure 10		-	10	-	kΩ
Undervolta	ge <sup>[9]</sup>						
V <sub>BG(uv)</sub>	battery-ground undervoltage		[11]	2	4.2	5.3	V
V <sub>BG(uv)(hys)</sub>	battery-ground undervoltage hysteresis			-	0.5	1.5	V
Overvoltag	e <sup>[9]</sup>						
V <sub>BG(ov)</sub>	battery-ground overvoltage		[12]	35	40	45	V
V <sub>BG(ov)(hys)</sub>	battery-ground overvoltage hysteresis			0.2	1	2	V
I <sub>G(ov)</sub>	overvoltage operating current	V <sub>BG</sub> = 45 V; per channel		-	1	2.5	mA
Overload p	rotection						
I <sub>L(lim)</sub>	self-limiting load current	$V_{BG} \ge 8 \text{ V}; \text{ V}_{BL} = V_{BG}; \text{ Figure 7}$		8	12	16	А
Overtempe	erature protection <sup>[9][10]</sup>						
T <sub>j(th)</sub>	threshold junction temperature		[13]	150	170	190	°C
T <sub>j(th)(hys)</sub>	threshold junction temperature hysteresis			3	10	20	°C
Status <sup>[9]</sup>							
V <sub>SG(CL)</sub>	status-ground clamping voltage	I <sub>S</sub> = 100 μA		5.5	7	8.5	V
V <sub>SG(L)</sub>	status-ground low voltage	I <sub>S</sub> = 100 μA; <mark>Figure 6</mark>		-	0.7	0.9	V
		I <sub>S</sub> = 250 μA		-	-	1.1	V
I <sub>S(off)</sub>	status leakage current	$V_{SG} = 5 V$					
		T <sub>mb</sub> = 150 °C		-	-	10	μΑ
		T <sub>mb</sub> = 25 °C		-	0.1	1	μΑ
R <sub>S</sub>	status resistor	V <sub>SG</sub> = 5 V; connected externally; Figure 10	[14]	-	47	-	kΩ

#### Table 7: Static characteristics...continued

[1] For a high-side switch, the load pin voltage goes negative with respect to the ground during the turn-off of an inductive load. This negative voltage is clamped by the device.

 $[2] \quad 9~V \leq V_{BG} \leq 35~V$ 

[3] This is the current drawn from the supply when both inputs are LOW, and includes leakage current to the loads.

[4] Defined as in ISO10483-1. For comparison purposes only.

[5] This only applies to the  $R_{BLon}$  per channel. The supply and input voltages for the  $R_{BLon}$  tests are continuous. The specified pulse duration is  $t_p = 300 \,\mu$ s, and refers only to the applied load current.

[6]  $R_G$  is a resistor incorporated internally into the package.

 $[7] \quad 5.5 \text{ V} \leq \text{V}_{BG} \leq 35 \text{ V}$ 

[8] An open circuit load can be detected in the off-state and requires an external pull-up resistor, R<sub>L(oc)</sub>.

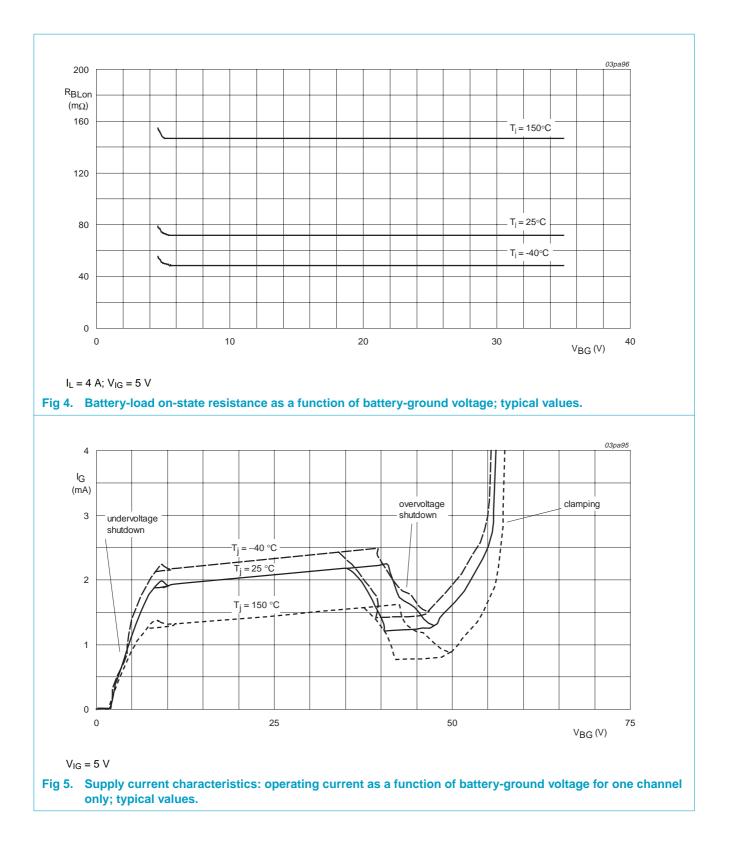
[9] See Table 4 "Truth table"

- [10] Overtemperature protection is not active during reverse current operation.
- [11] Undervoltage sensor causes each output channel to switch off and reset.
- [12] Overvoltage sensor causes each output channel to switch off to protect the load.
- [13] After cooling below the reset temperature the channel will resume normal operation.

[14] The status output is an open drain transistor and requires an external pull-up resistor, R<sub>S</sub>, to indicate a logic HIGH.

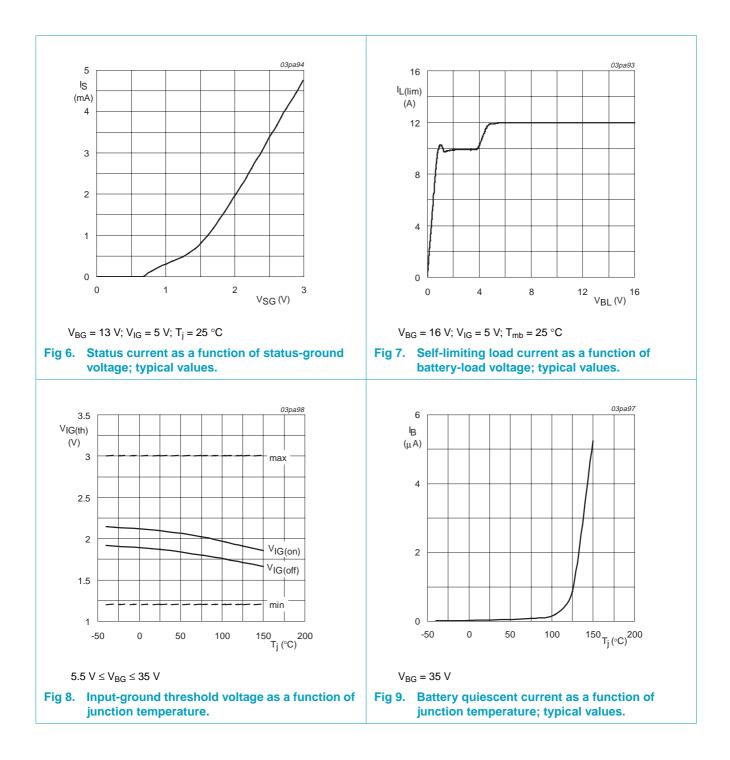
# PIP3224-DC

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## 9. Dynamic characteristics

#### Table 8: Switching characteristics

 $T_{mb} = 25 \circ C$ ;  $V_{BG} = 13 V$ ; resistive load  $R_L = 13 \Omega$  per channel; Figure 12.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Turn-on m	neasured from the input going H	ligh				
t <sub>d(on)</sub>	turn-on delay time	to 10 % V <sub>L</sub>	-	30	-	μs
dV/dt <sub>on</sub>	rising slew rate	30 to 70 % $V_L$	0.5	1	2	V/µs
t <sub>on</sub>	turn-on switching time	to 90 % V <sub>L</sub>	-	60	220	μs
Turn-off n	neasured from the input going L	LOW				
t <sub>d(off)</sub>	turn-off delay time	to 90 % V <sub>L</sub>	-	20	-	μs
dV/dt <sub>off</sub>	falling slew rate	70 to 30 % $V_L$	0.5	1	2	V/µs
t <sub>off</sub>	turn-off switching time	to 10 % V <sub>L</sub>	-	40	200	μs

#### Table 9: Capacitances

 $T_{mb} = 25 \circ C; f = 1 MHz; V_{IG} = 0 V.$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>sg</sub>	status-ground capacitance	$V_{SG} = 5 V$	-	11	15	pF
Per chann	el					
C <sub>ig</sub>	input-ground capacitance	V <sub>BG</sub> = 13 V	-	15	20	pF
C <sub>bl</sub>	battery-load capacitance	V <sub>BL</sub> = 13 V	-	130	180	pF

#### Table 10: Short circuit load protection characteristics

#### $T_{mb} \leq 125 \circ C$ prior to the overload short circuit condition.

ine	1						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P <sub>BL(OV)(th)</sub>	battery-load overload power threshold		[1]	10	55	100	W
t <sub>BL(d)(sc)</sub>	battery-load short-circuit characteristic time	P <sub>BL</sub> > P <sub>BL(OV)(th)</sub> ; Figure 11	[2]	200	350	800	μs

[1] Short circuit protection is latched, but at high temperatures where  $T_j > T_{j(th)}$  overtemperature protection may occur first. Normal operation may only be resumed following a short circuit after the input is toggled LOW then HIGH again.

[2] Short circuit response time  $t_{d(sc)}$  varies with battery-load power  $P_{BL}$  according to the **logarithmic model** equation:

$$t_{d(sc)} \approx \frac{t_{BL(d)(sc)}}{ln\left(\frac{P_{BL}}{P_{BL(OV)(th)}}\right)}$$

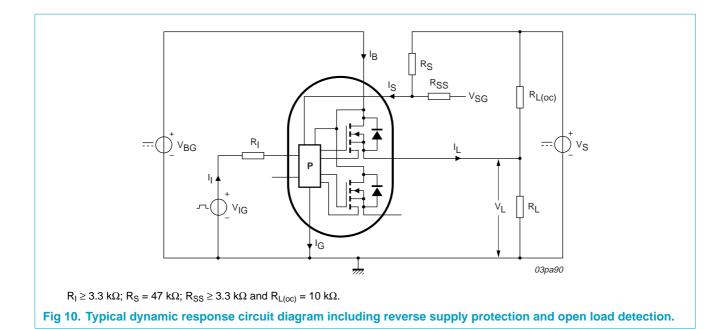
#### Table 11: Status response times

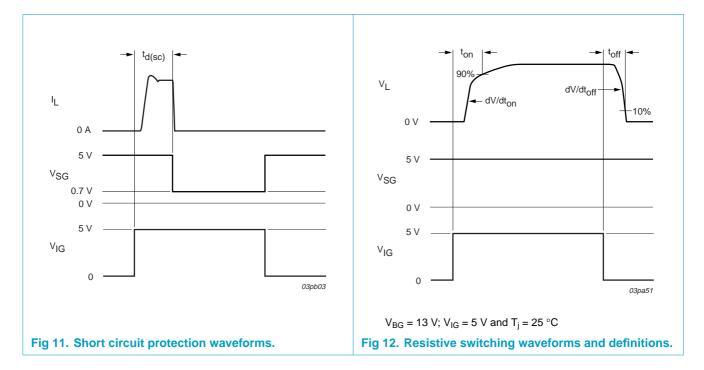
Limits are valid for  $-40 \circ C \le T_{mb} \le +150 \circ C$  and typical values for  $T_{mb} = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Measured	from when the input goes LOW	to when the status goes LOW				
t <sub>d(oc)</sub>	open-circuit response time	Figure 10 and 14	-	65	100	μs

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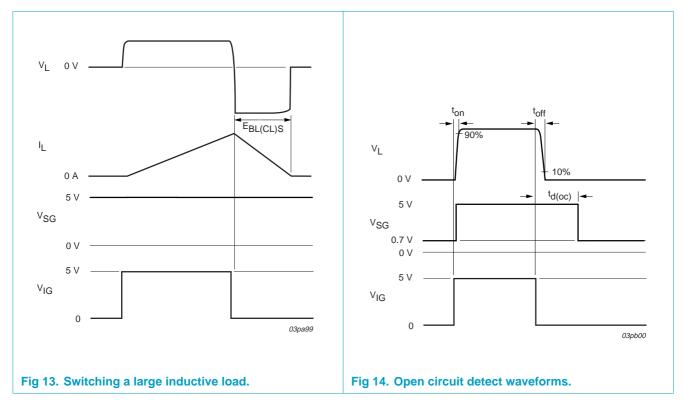
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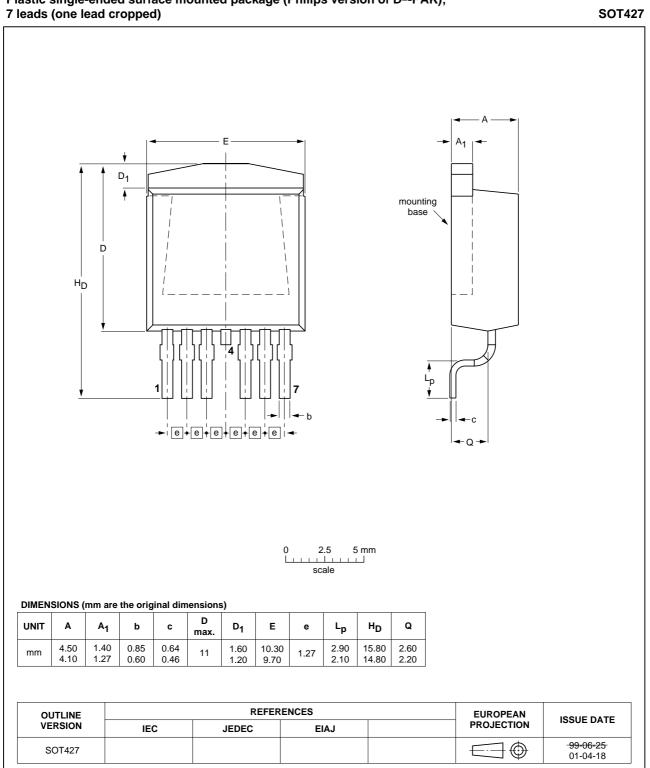
# **10. Package information for SOT427**

Epoxy meets requirements of UL 94 V-0 at 1/8 inch thickness. Net mass: 1.5 g. For soldering guidelines and surface mount footprint design, please visit http://www.semiconductors.philips.com/package/

# **PIP3224-DC**

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## 11. Package outline



# Plastic single-ended surface mounted package (Philips version of D<sup>2</sup>-PAK);

Fig 15. SOT427 (D<sup>2</sup>-PAK).

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# **12. Revision history**

Table 12: Revision history						
Rev	Date	CPCN	Description			
01	20040220	-	Product data (9397 750 12362)			

#### Dual channel high-side TOPFET™

## 13. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2][3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## 14. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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## **Contact information**

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